

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C		
201/	7.5mΩ @ V _{GS} = -10V	-12A		
-30V	10.2mΩ @ V _{GS} = -4.5V	-10A		

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

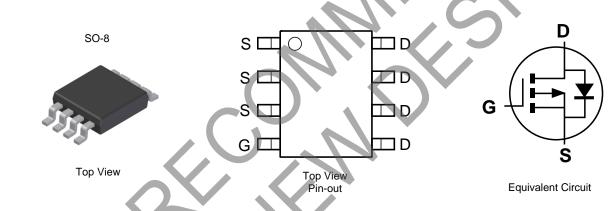
30V P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMG4413LSSQ</u>)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead
 Frame. Solderable per MIL-STD-202, Method 208 (e3)
 - Weight: 0.074 grams (Approximate)



Ordering Information (Note 4)

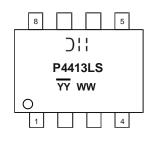
	Part Number	Case	Packaging			
DMG4413LSS-13		SO-8	2500/Tape & Reel			
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



8	\square	\square	5		
	С				
P4413LS					
	YY	ww			
0					
1			4		

);; = Manufacturer's Marking
 P4413LS = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 18 = 2018)
 WW = Week (01 to 53)
 YY = Date Code Marking for SAT (Shanghai Assembly/ Test Site)
 YY = Date Code Marking for CAT (Chengdu Assembly/ Test Site)

Chengdu A/T Site

Shanghai A/T Site

DMG4413LSS Document number: DS31754 Rev. 7 - 3



DMG4413LSS

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-12 -10	А
Continuous Drain Current (Note 6) V_{GS} = -10V	t<10s	T _A = +25°C T _A = +70°C	ID	-22 -17	А
	Steady State	T _A = +25°C T _A = +70°C	ID	-10 -8	А
Continuous Drain Current (Note 6) $V_{GS} = -4.5$	t<10s	T _A = +25°C T _A = +70°C	ID	-18 -14	А
Pulsed Drain Current (10µs Pulse, Duty Cycle =	I _{DM}	-45	А		
Maximum Body Diode Continuous Current	ls	-4	А		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	PD	1.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State t<10s	Reja	74 22	°C/W
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	PD	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State t<10s	R _{0JA}	56 17	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	R _{0JC}	2.5	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_		V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	IDSS			-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	IGSS			±1	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
Static Drain-Source On-Resistance			6.3	7.5	mΩ	$V_{GS} = -10V, I_D = -13A$
Static Drain-Source On-Resistance	R _{DS(ON)}	—	7.9	10.2	1115.2	$V_{GS} = -4.5V, I_D = -10A$
Forward Transconductance	g fs		26		S	$V_{DS} = -15V, I_D = -13A$
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -2.7A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		4965		pF	
Output Capacitance	Coss		1487		pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss		711	_	pF	
Gate Resistance	R_G	_	7.3	—	Ω	$V_{DS} = 0V, V_{GS} = 0V$ f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q _G		46	—		V _{DS} = -15V, V _{GS} = -5V I _D = -13A
Gate-Source Charge	Q _{GS}		17	_	nC	
Gate-Drain Charge	Q _{GD}		16			
Turn-On Delay Time	t _{D(ON)}		15			$V_{DS} = -15V, V_{GS} = -10V,$ $I_D = -1A, R_G = 6.0\Omega$
Rise Time	t _R		9	—		
Turn-Off Delay Time	t _{D(OFF)}		160		ns	
Fall Time	t _F		66			

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

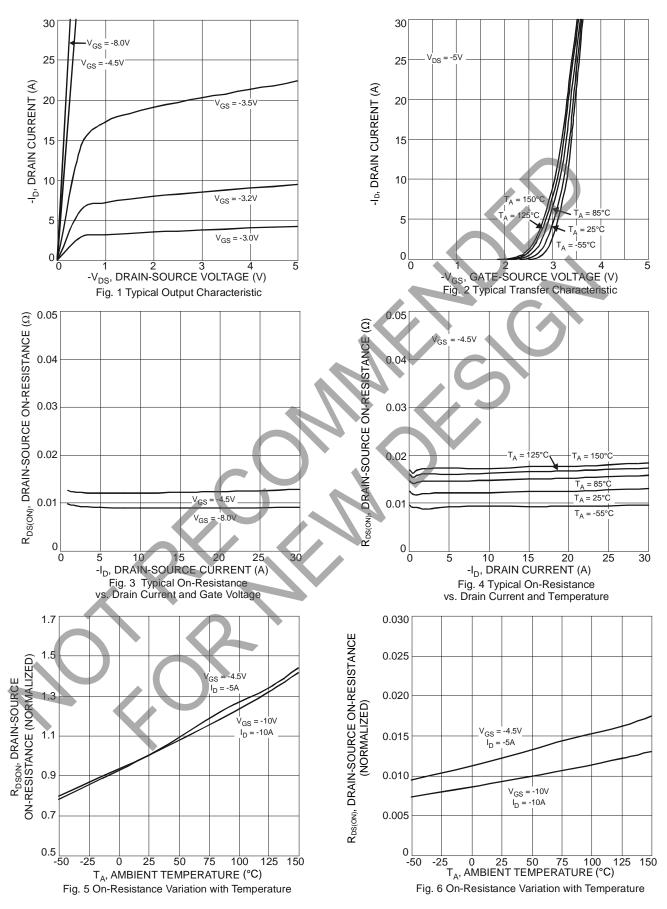
Notes:

Downloaded From Oneyac.com

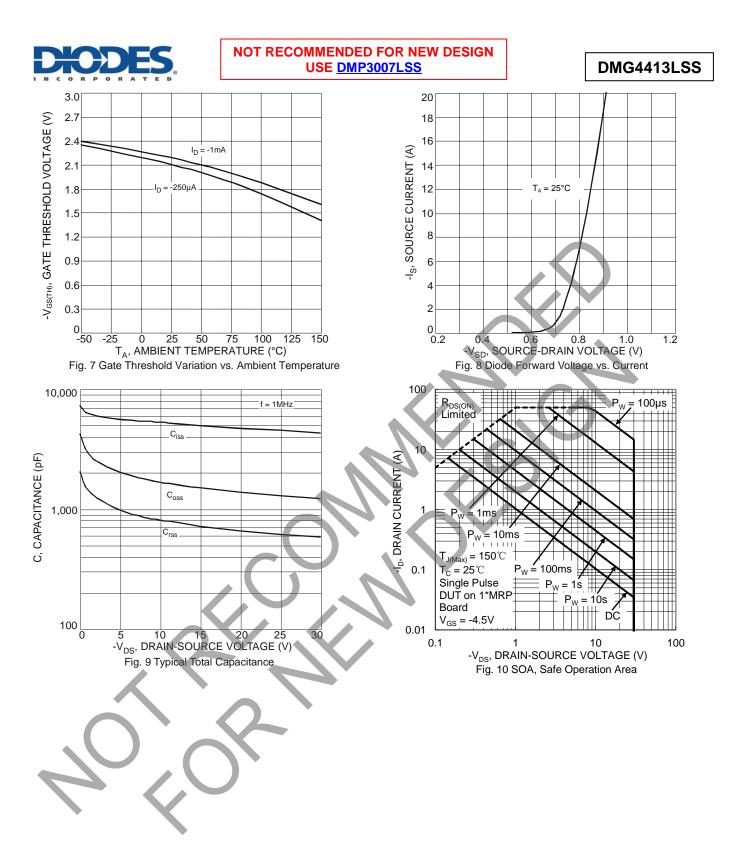


NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3007LSS</u>





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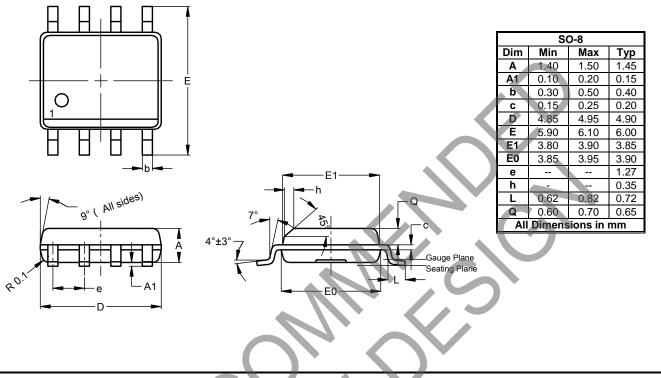




Package Outline Dimensions

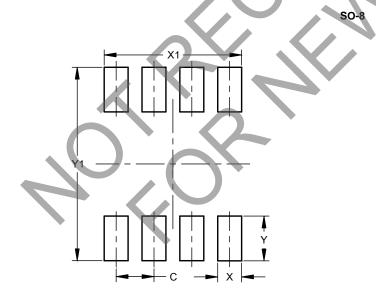
Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
C	1.27
Х	0.802
X1	4.612
Y	1.505
Y1	6.50



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